

ABSTRACT OF THE DISCLOSURE

A nonvolatile semiconductor memory device includes cell transistors connected to a plurality of wirings, word lines each commonly connected to the gate electrodes of those of the cell transistors which are arranged on a corresponding row, and driving circuits respectively connected to the plurality of wirings. The driving circuit includes a detection circuit which detects threshold voltage of the cell transistor in a verify operation, a storage circuit which stores threshold voltage detected and a potential setting circuit which sets potential of the wiring to at least three potentials based on the threshold voltage stored in the storage circuit in a program operation following the verify operation.